VS-VSKT105..., VS-VSKH105..., VS-VSKL105..., VS-VSKN105... Series

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AAP Gen 7 (TO-240AA) Power Modules Thyristor/Diode and Thyristor/Thyristor, 105 A



ADD-A-PAK

PRIMARY CHARACTERISTICS					
I _{T(AV)} or I _{F(AV)}	105 A				
Туре	Modules - thyristor, standard				
Package	AAP Gen 7 (TO-240AA)				

MECHANICAL DESCRIPTION

The AAP Gen 7 (TO-240AA), new generation of APP module, combines the excellent thermal performances obtained by the usage of exposed direct bonded copper substrate, with advanced compact simple package solution and simplified internal structure with minimized number of interfaces.

FEATURES

- · High voltage
- Industrial standard package



- · Low thermal resistance
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

BENEFITS

- Excellent thermal performances obtained by the usage of exposed direct bonded copper substrate
- Up to 1600 V
- · High surge capability
- · Easy mounting on heatsink

ELECTRICAL DESCRIPTION

These modules are intended for general purpose high voltage applications such as high voltage regulated power supplies, lighting circuits, temperature and motor speed control circuits, UPS and battery charger.

MAJOR RATINGS AND CHARACTERISTICS							
SYMBOL	CHARACTERISTICS VALUES		UNITS				
I _{T(AV)} or I _{F(AV)}	85 °C	105					
I _{O(RMS)}	As AC switch	235	Α				
I _{TSM,}	50 Hz	2000	A				
I _{FSM}	60 Hz	2094					
l ² t	50 Hz	20	kA ² s				
1-1	60 Hz	18.26	KA-S				
I ² √t		200	kA²√s				
V _{DRM} /V _{RRM}	Range	400 to 1600	V				
T _{Stg}		-40 to +130	°C				
T _J	-40 to +130		C				

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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS								
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM,} I _{DRM} AT 130 °C mA			
	04	400	500	400				
	06	600	700	600				
	08	800	900	800				
VS-VSK.105	10	1000	1100	1000	20			
	12	1200	1300	1200				
	14	1400	1500	1400				
	16	1600	1700	1600				

ON-STATE CONDUCTION						
PARAMETER	SYMBOL		TEST CONDITIONS			UNITS
Maximum average on-state current (thyristors)	I _{T(AV)}	180° conduction	on, half sine wa	/e,	105	
Maximum average forward current (diodes)	I _{F(AV)}	T _C = 85 °C			105	
Maximum continuous RMS on-state current, as AC switch	I _{O(RMS)}		or ~	I _(RMS)	235	Α
		t = 10 ms	No voltage		2000	
Maximum peak, one-cycle non-repetitive	I _{TSM}	t = 8.3 ms	reapplied	Sinusoidal	2094	
on-state or forward current	or I _{ESM}	t = 10 ms	100 % V _{RRM}	half wave, initial $T_{.1} = T_{.1}$ maximum	1682	
	T OW	t = 8.3 ms	reapplied	. 0 0	1760	
		t = 10 ms	No voltage		20	
Maximum I ² t for fusing	l ² t	t = 8.3 ms	reapplied	latital T. T. association	18.26	kA ² s
	I-ί	t = 10 ms	100 % V _{RRM}	Initial $T_J = T_J$ maximum	14.14	
		t = 8.3 ms	reapplied		12.91	
Maximum I ² √t for fusing	I ² √t ⁽¹⁾		$t = 0.1$ ms to 10 ms, no voltage reapplied $T_J = T_J$ maximum			kA ² √s
Maximum value or threshold voltage	V _{T(TO)} (2)	Low level (3)	T. T. and the ar		0.98	V
Maximum value of threshold voltage	VT(TO) (=)	High level (4)	$T_J = T_J \text{ maxin}$	IUIII	1.12	V
Maximum value of on-state	r _t ⁽²⁾	Low level (3)	T _ T movin	21172	2.7	m()
slope resistance	I t (-)	High level (4)	$T_J = T_J$ maximum		2.34	mΩ
Maximum peak on-state or forward voltage	V_{TM}	$I_{TM} = \pi \times I_{T(AV)}$	T _J = 25 °C		1.8	V
waximum peak on-state or forward voltage	V_{FM}	$I_{FM} = \pi \times I_{F(AV)}$	1J = 25 C		1.0	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$T_J = 25$ °C, from 0.67 V_{DRM} , $I_{TM} = \pi \ x \ I_{T(AV)}$, $I_g = 500$ mA, $t_r < 0.5$ μs , $t_p > 6$ μs			150	A/μs
Maximum holding current	I _H	T _J = 25 °C, anode supply = 6 V, resistive load, gate open circuit			250	mA
Maximum latching current	ΙL	T _J = 25 °C, and	ode supply = 6	V, resistive load	400	

Notes

⁽¹⁾ I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$

⁽²⁾ Average power = $V_{T(TO)} \times I_{T(AV)} + r_t \times (I_{T(RMS)})^2$

 $^{^{(3)}}$ 16.7 % x π x I_{AV} < I < π x I_{AV}

⁽⁴⁾ $I > \pi \times I_{AV}$

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TRIGGERING						
PARAMETER	SYMBOL	TEST CO	ONDITIONS	VALUES	UNITS	
Maximum peak gate power	P _{GM}			12	W	
Maximum average gate power	P _{G(AV)}			3	VV	
Maximum peak gate current	I _{GM}			3	Α	
Maximum peak negative gate voltage	- V _{GM}			10		
Maximum gate voltage required to trigger		T _J = -40 °C	Anode supply = 6 V resistive load	4.0	V	
	V_{GT}	T _J = 25 °C		2.5		
		T _J = 125 °C		1.7		
		T _J = -40 °C		270		
Maximum gate current required to trigger	I _{GT}	T _J = 25 °C	Anode supply = 6 V resistive load	150	mA	
		T _J = 125 °C	- resistive load	80		
Maximum gate voltage that will not trigger	V_{GD}	T _J = 125 °C, rated V _{DRM} applied		0.25	V	
Maximum gate current that will not trigger	I_{GD}	T _J = 125 °C, rated V _{DRM} applied		6	mA	

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Maximum peak reverse and off-state leakage current at V _{RRM} , V _{DRM}	I _{RRM,} I _{DRM}	T _J = 130 °C, gate open circuit	20	mA				
Maximum RMS insulation voltage V _{II}		50 Hz	3000 (1 min) 3600 (1 s)	V				
Maximum critical rate of rise of off-state voltage	dV/dt	T _J = 130 °C, linear to 0.67 V _{DRM}	1000	V/µs				

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER		SYMBOL	SYMBOL TEST CONDITIONS		UNITS		
Junction operating temperature ra	Junction operating temperature range			-40 to +130	°C		
Storage temperature range		T _{Stg}		-40 10 +130)		
Maximum internal thermal resistance, junction to case per leg		R _{thJC}	DC operation	0.22	°C/W		
Typical thermal resistance, case to heatsink per module		R _{thCS}	Mounting surface flat, smooth and greased	0.1	C/VV		
	to heatsink		A mounting compound is recommended and the torque should be rechecked after a period	4			
Mounting torque ± 10 % busbar			of 3 hours to allow for the spread of the compound.	3	Nm		
Approximate weight				75	g		
Approximate weight	Approximate weight			2.7	OZ.		
Case style			JEDEC®	AAP Gen 7	(TO-240AA)		

△R CONDUCTION PER JUNCTION											
DEVICES	5	SINE HALF	WAVE CO	NDUCTION	N	RECTANGULAR WAVE CONDUCTION				LINUTO	
DEVICES	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	UNITS
VSK.105	0.04	0.048	0.063	0.085	0.125	0.033	0.052	0.067	0.088	0.127	°C/W

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

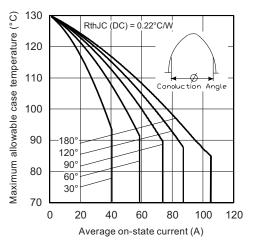


Fig. 1 - Current Ratings Characteristics

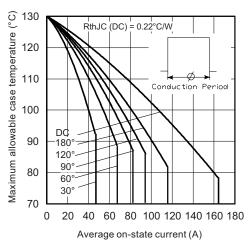


Fig. 2 - Current Ratings Characteristics

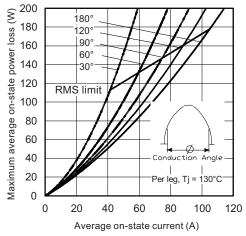


Fig. 3 - On-State Power Loss Characteristics

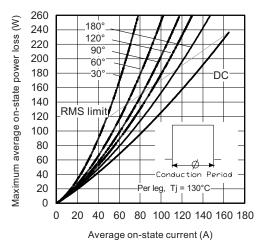


Fig. 4 - On-State Power Loss Characteristics

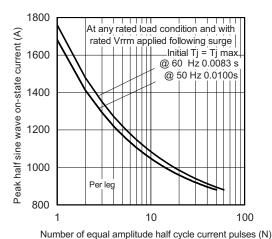


Fig. 5 - Maximum Non-Repetitive Surge Current

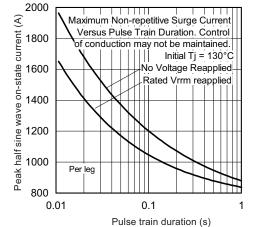


Fig. 6 - Maximum Non-Repetitive Surge Current

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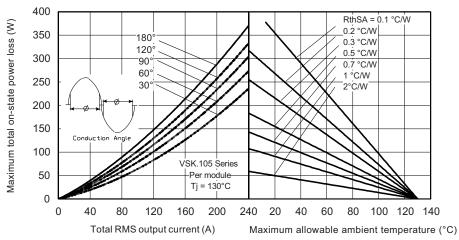


Fig. 7 - On-State Power Loss Characteristics

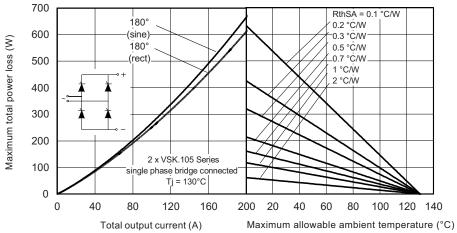


Fig. 8 - On-State Power Loss Characteristics

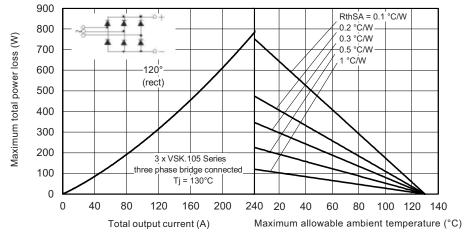


Fig. 9 - On-State Power Loss Characteristics

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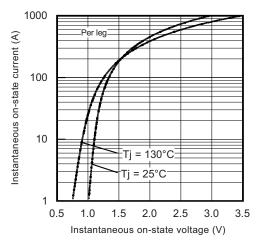


Fig. 10 - On-State Voltage Drop Characteristics

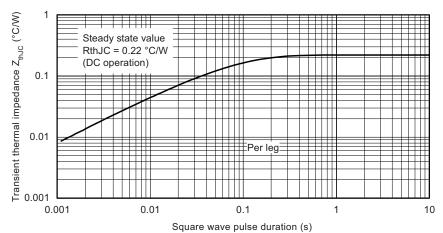


Fig. 11 - Thermal Impedance Z_{thJC} Characteristics

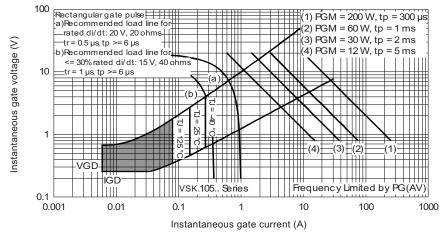
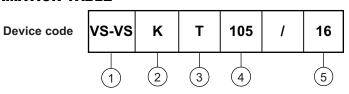


Fig. 12 - Gate Characteristics

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ORDERING INFORMATION TABLE



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2 - Module type

- Circuit configuration (see Circuit Configuration table)

4 - Current code (105 A)

- Voltage code (see Voltage Ratings table)

Note

To order the optional hardware go to www.vishay.com/doc?95172

CIRCUIT CONFIGURATION	CIRCUIT CONFIGURATION CODE	CIRCUIT DRAWING
Two SCRs doubler circuit	Т	VSKT (1) (2) (2) (3) (3) (3) (4) (6) (7) (6)
SCR/diode doubler circuit, positive control	н	VSKH (2) (2) (3) (3) (4) (5) (4) (5)
SCR/diode doubler circuit, negative control	L	VSKL (1) (2) (2) (2) (2) (3) (6) (7) (6)
SCR/diode common anodes	N	VSKN 1

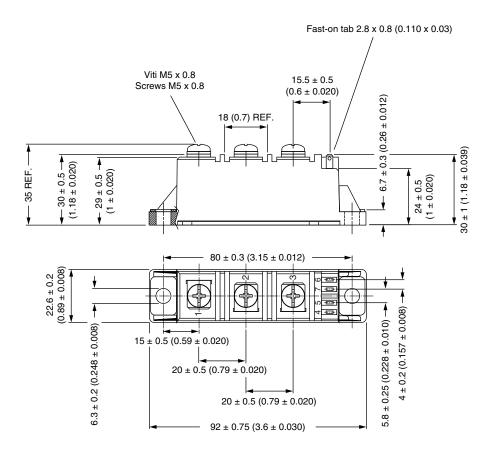
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95368				
I Dimensions	www.vishay.com/doc?95368				



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ADD-A-PAK Generation VII - Thyristor

DIMENSIONS in millimeters (inches)





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